

1N5817 - 1N5819

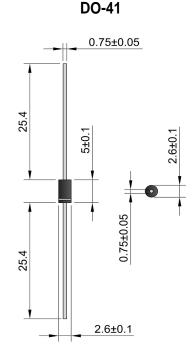
1.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Guard Ring for Transient and ESD Protection
- Surge Overload Rating to 25A Peak
- Low Power Loss, High Efficiency
- Ideally Suited for Use in High Frequency SMPS, Inverters and As Free Wheeling Diodes

Mechanical Data

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version



Maximum Ratings and Electrical Characteristics @T_=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

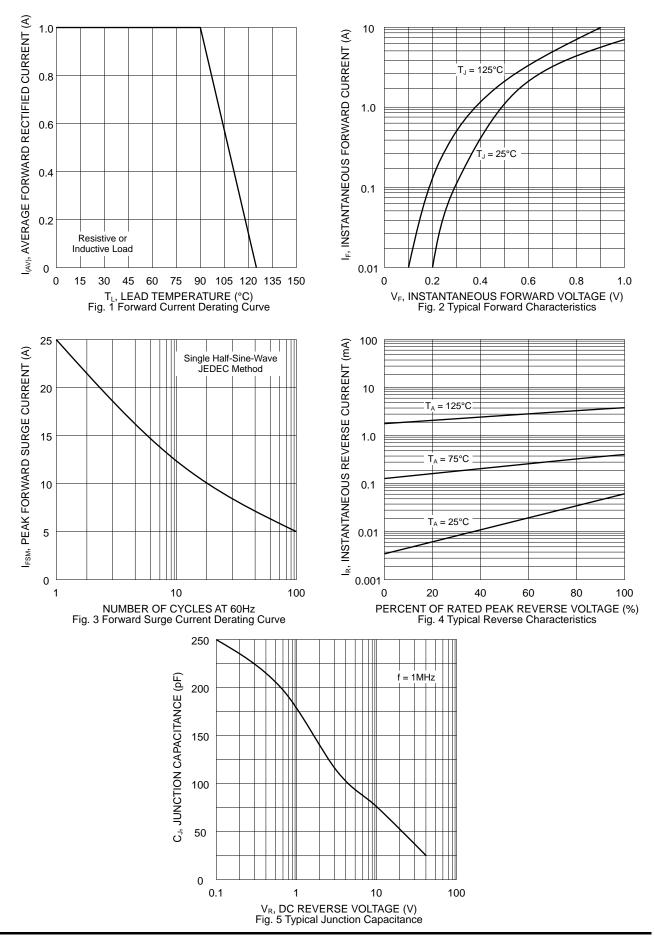
Characteristic	Symbol	1N5817	1N5818	1N5819	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	V
RMS Reverse Voltage	VR(RMS)	14	21	28	V
Average Rectified Output Current (Note 1) $@T_L = 90^{\circ}C$	lo	1.0			А
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	IFSM	25			A
Forward Voltage $@I_F = 1.0A$ $@I_F = 3.0A$	Vfm	0.450 0.750	0.550 0.875	0.600 0.900	V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Irm	1.0 10			mA
Typical Junction Capacitance (Note 2)	CJ	110			pF
Thermal Resistance, Junction to Ambient (Note 3) Thermal Resistance, Junction to Lead (Note 3)	R JA R JL	50 15			°C/W
Operating Temperature Range	TJ	-65 to +125			°C
Storage Temperature Range	Тѕтс	-65 to +150			°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

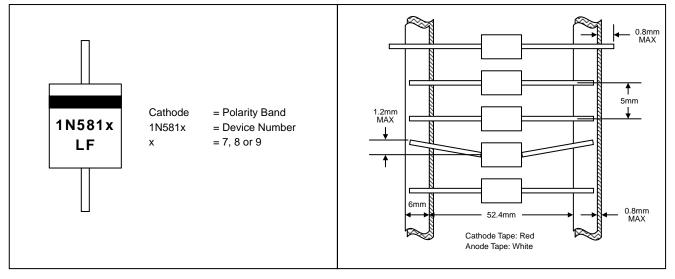
3. Vertical PCB mounting with 9.5mm lead length on 38 x 38mm copper pad.







MARKING INFORMATION



TAPING SPECIFICATIONS

PACKAGING INFORMATION

